

# RJK60S4DPE

600V - 16A - SJ MOS FET  
High Speed Power Switching

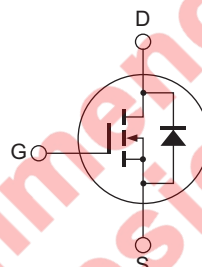
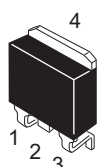
R07DS0733EJ0200  
Rev.2.00  
Oct 12, 2012

## Features

- Superjunction MOSFET
- Low on-resistance  
 $R_{DS(on)} = 0.23 \Omega$  typ. (at  $I_D = 8 \text{ A}$ ,  $V_{GS} = 10 \text{ V}$ ,  $T_a = 25^\circ\text{C}$ )
- High speed switching  
 $t_f = 21 \text{ ns}$  typ. (at  $I_D = 8 \text{ A}$ ,  $V_{GS} = 10 \text{ V}$ ,  $R_L = 37.5 \Omega$ ,  $R_g = 10 \Omega$ ,  $T_a = 25^\circ\text{C}$ )

## Outline

RENESAS Package code: PRSS0004AE-B  
(Package name: LDKAK(S)-(1) )



1. Gate
2. Drain
3. Source
4. Drain

## Absolute Maximum Ratings

( $T_a = 25^\circ\text{C}$ )

Item	Symbol	Ratings	Unit
Drain to source voltage	$V_{DSS}$	600	V
Gate to source voltage	$V_{GSS}$	+30, -20	V
Drain current	$T_c = 25^\circ\text{C}$ $I_D$ <sup>Note1</sup>	16	A
	$T_c = 100^\circ\text{C}$ $I_D$ <sup>Note1</sup>	10.1	A
Drain peak current	$I_{D(pulse)}$ <sup>Note1</sup>	32	A
Body-drain diode reverse drain current	$I_{DR}$ <sup>Note1</sup>	16	A
Body-drain diode reverse drain peak current	$I_{DR(pulse)}$ <sup>Note1</sup>	32	A
Avalanche current	$I_{AP}$ <sup>Note2</sup>	4	A
Avalanche energy	$E_{AR}$ <sup>Note2</sup>	0.87	mJ
Channel dissipation	$P_{ch}$ <sup>Note3</sup>	104.1	W
Channel to case thermal impedance	$\theta_{ch-c}$	1.2	$^\circ\text{C/W}$
Channel temperature	$T_{ch}$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

Notes: 1. Limited by  $T_{ch}$  max.  
2.  $ST_{ch} = 25^\circ\text{C}$ ,  $T_{ch} \leq 150^\circ\text{C}$   
3. Value at  $T_c = 25^\circ\text{C}$

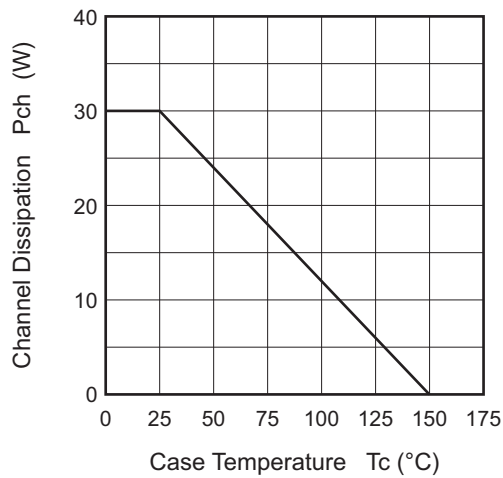
## Electrical Characteristics

(Ta = 25°C)

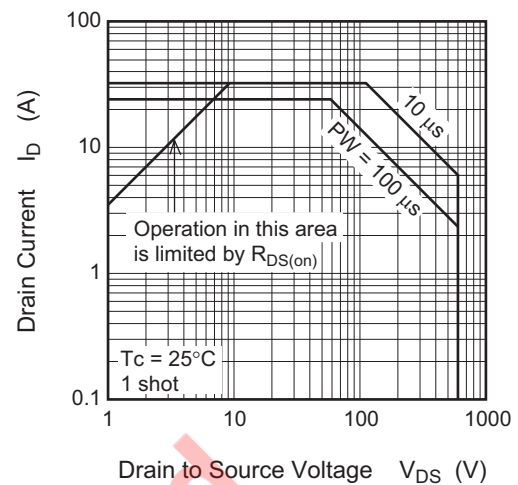
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	600	—	—	V	$I_D = 10 \text{ mA}$ , $V_{GS} = 0$
Zero gate voltage drain current	$I_{DSS}$	—	—	1	mA	$V_{DS} = 600 \text{ V}$ , $V_{GS} = 0$
Gate to source leak current	$I_{GSS}$	—	—	$\pm 0.1$	$\mu\text{A}$	$V_{GS} = +30 \text{ V}$ , $-20 \text{ V}$ , $V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	3	—	5	V	$V_{DS} = 10 \text{ V}$ , $I_D = 1 \text{ mA}$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.23	0.29	$\Omega$	$I_D = 8 \text{ A}$ , $V_{GS} = 10 \text{ V}$ <sup>Note4</sup>
	$R_{DS(on)}$	—	0.57	—	$\Omega$	Ta = 150°C $I_D = 8 \text{ A}$ , $V_{GS} = 10 \text{ V}$ <sup>Note4</sup>
Gate resistance	$R_g$	—	2	—	$\Omega$	f = 1 MHz $V_{DS} = 25 \text{ V}$ , $V_{GS} = 0$
Input capacitance	$C_{iss}$	—	988	—	pF	$V_{DS} = 25 \text{ V}$
Output capacitance	$C_{oss}$	—	1415	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	$C_{rss}$	—	5.1	—	pF	f = 100kHz
Turn-on delay time	$t_{d(on)}$	—	15	—	ns	$I_D = 8 \text{ A}$
Rise time	$t_r$	—	19	—	ns	$V_{GS} = 10 \text{ V}$
Turn-off delay time	$t_{d(off)}$	—	30	—	ns	$R_L = 37.5 \Omega$
Fall time	$t_f$	—	17	—	ns	$R_g = 10 \Omega$ <sup>Note4</sup>
Total gate charge	$Q_g$	—	18	—	nC	$V_{DD} = 480 \text{ V}$
Gate to source charge	$Q_{gs}$	—	7	—	nC	$V_{GS} = 10 \text{ V}$
Gate to drain charge	$Q_{gd}$	—	6	—	nC	$I_D = 16 \text{ A}$ <sup>Note4</sup>
Body-drain diode forward voltage	$V_{DF}$	—	1.0	1.6	V	$I_F = 16 \text{ A}$ , $V_{GS} = 0$ <sup>Note4</sup>
Body-drain diode reverse recovery time	$t_{rr}$	—	363	—	ns	$I_F = 16 \text{ A}$
Body-drain diode reverse recovery current	$I_{rr}$	—	23	—	A	$V_{GS} = 0$
Body-drain diode reverse recovery charge	$Q_{rr}$	—	4.9	—	$\mu\text{C}$	$di_F/dt = 100 \text{ A}/\mu\text{s}$ <sup>Note4</sup>

Notes: 4. Pulse test

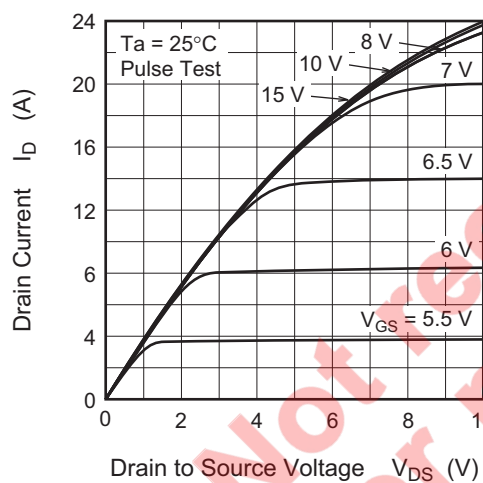
## Main Characteristics

Channel Dissipation vs.  
Case Temperature

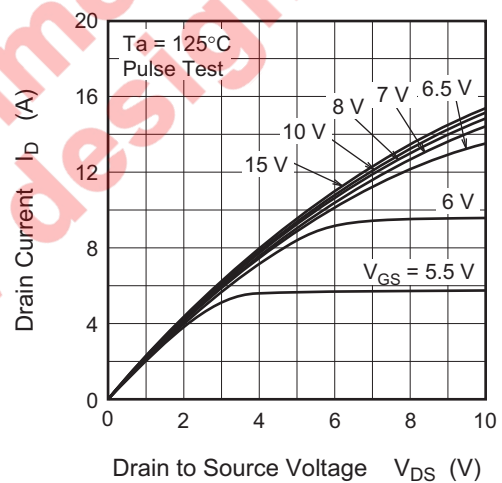
Maximum Safe Operation Area



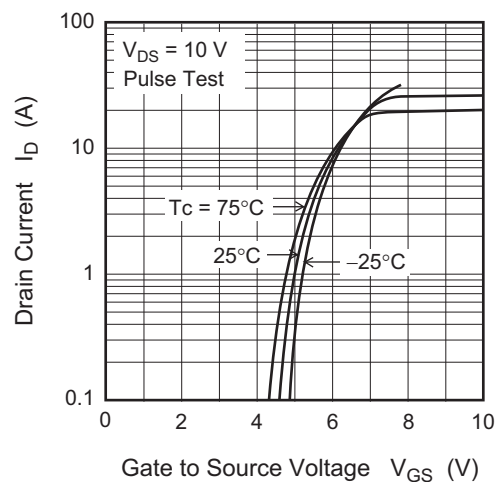
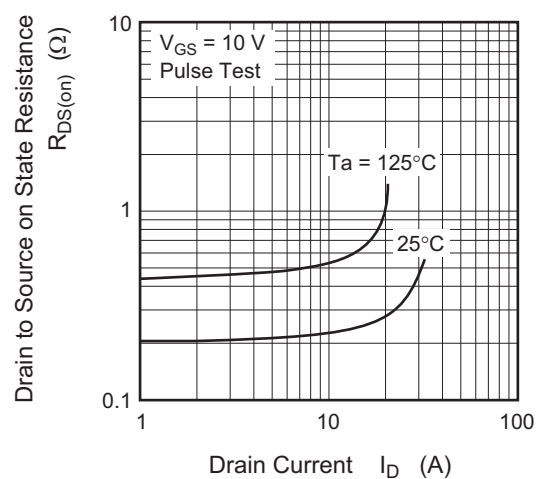
Typical Output Characteristics

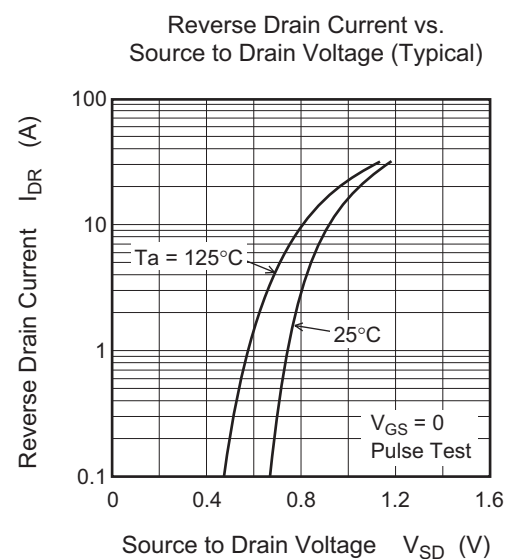
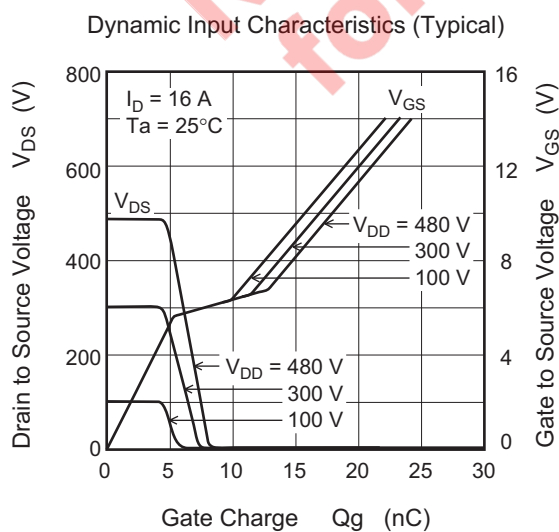
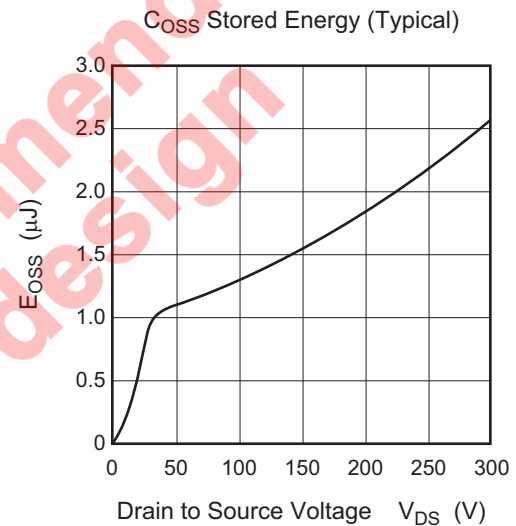
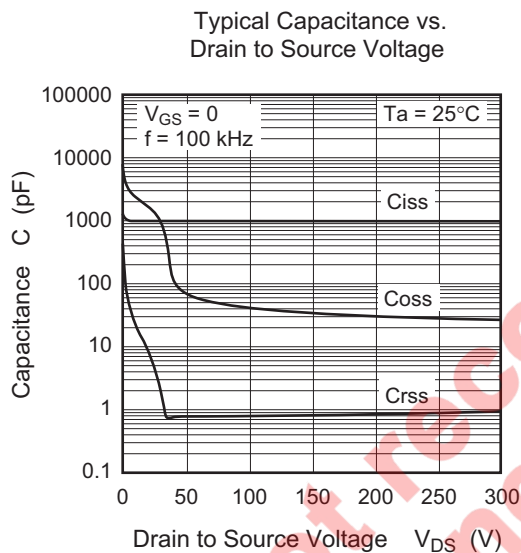
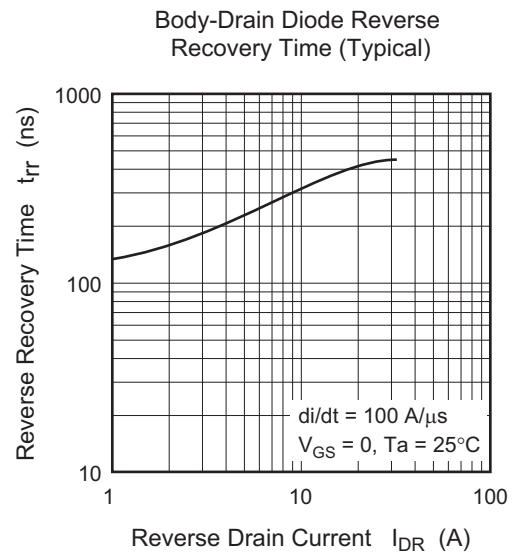
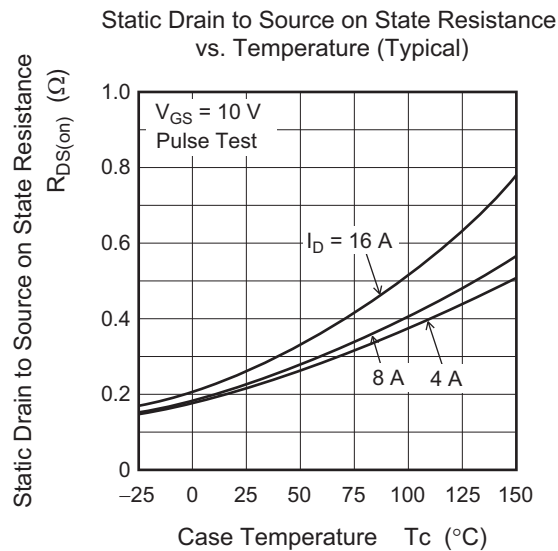


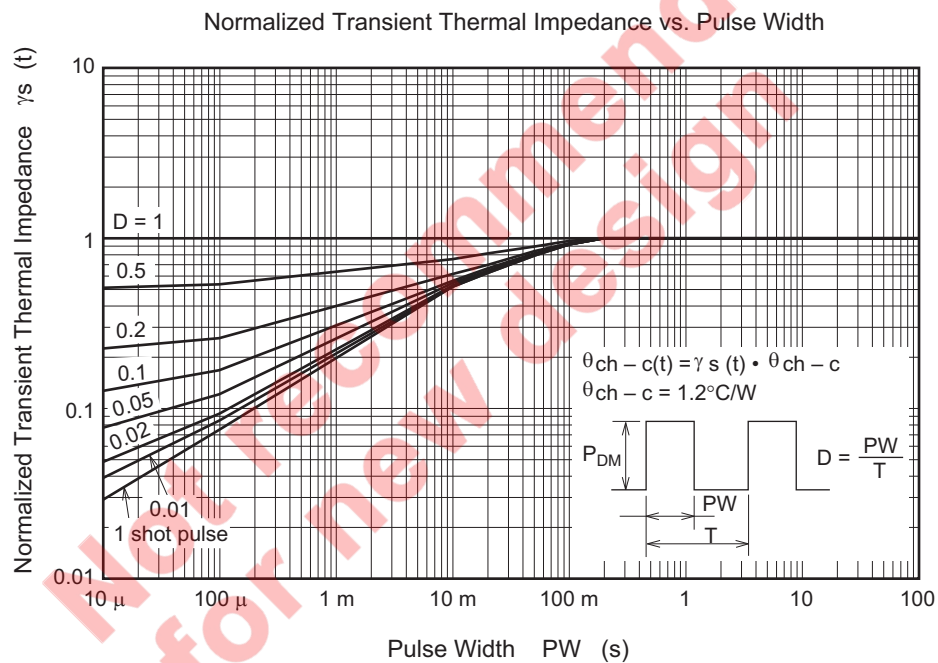
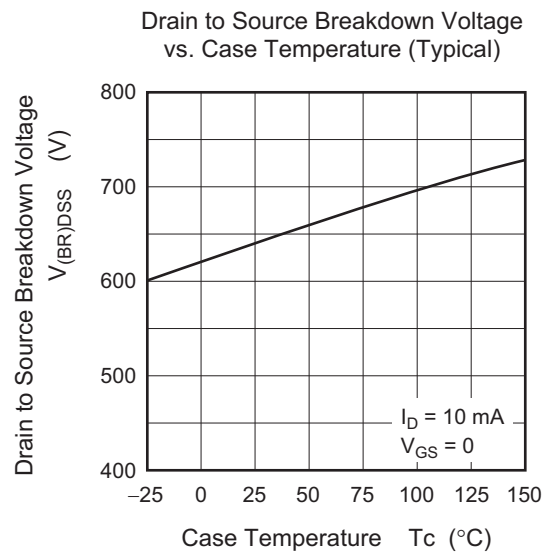
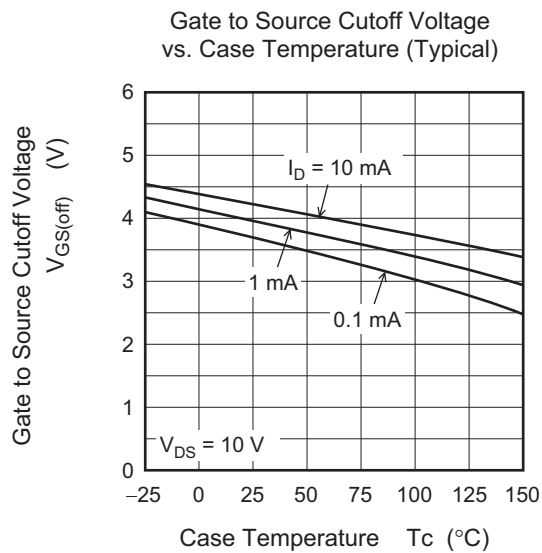
Typical Output Characteristics



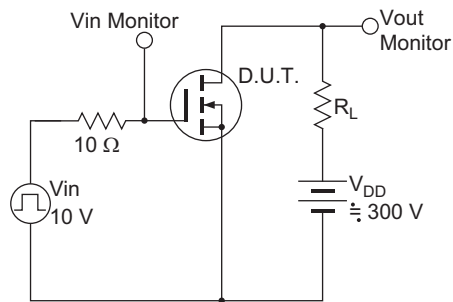
Typical Transfer Characteristics

Static Drain to Source on State Resistance  
vs. Drain Current (Typical)

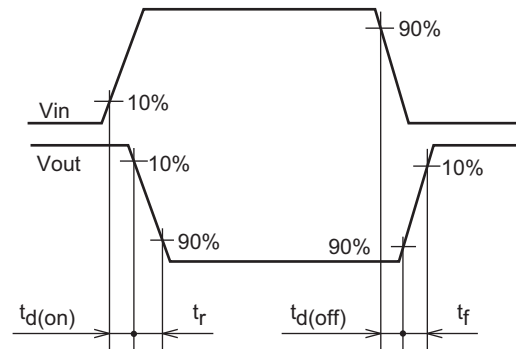




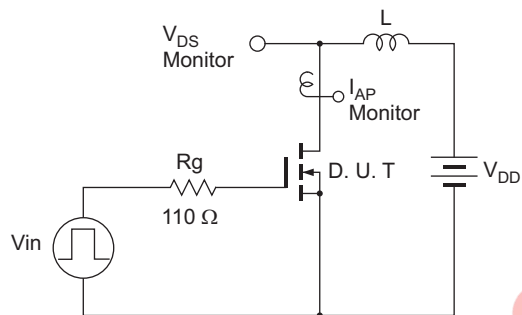
Switching Time Test Circuit



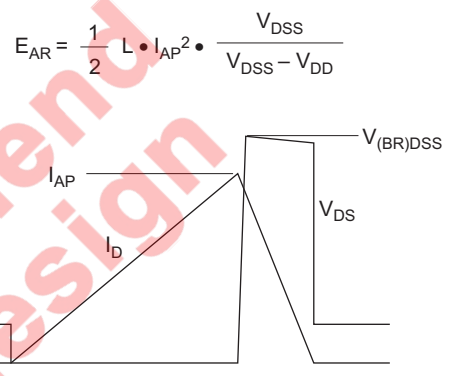
Waveform



Avalanche Test Circuit



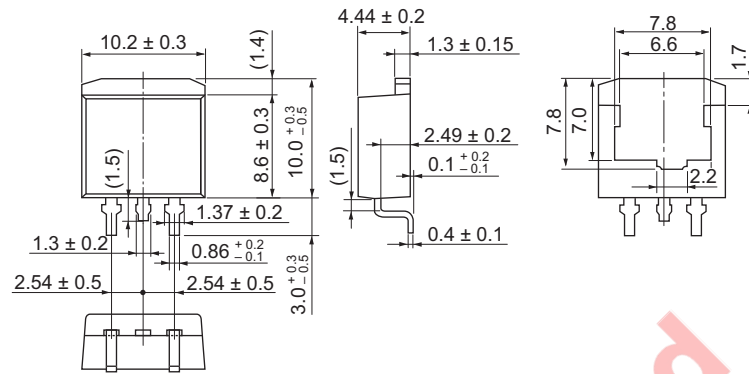
Avalanche Waveform



## Package Dimension

Package Name	JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
LDBPAK(S)-(1)	SC-83	PRSS0004AE-B	LDBPAK(S)-(1) / LDBPAK(S)-(1)V	1.30g

Unit: mm



## Ordering Information

Orderable Part No.	Quantity	Shipping Container
RJK60S4DPE-00#J3	1000 pcs	Taping

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